

# RD07MVS1B

RoHS Compliance, Silicon MOSFET Power Transistor, 175MHz, 520MHz, 7W

## DESCRIPTION

RD07MVS1B is a MOS FET type transistor specifically designed for VHF/UHF RF power amplifiers applications.

RD07MVS1B improved a drain surge than RD07MVS1 by optimizing MOSFET structure.

## FEATURES

High power gain:

$P_{out} > 7W$ ,  $G_p > 10dB$

@ $V_{dd} = 7.2V$ ,  $f = 520MHz$

High Efficiency: 60%typ. (175MHz)

High Efficiency: 55%typ. (520MHz)

## APPLICATION

For output stage of high power amplifiers in VHF/UHF band mobile radio sets.

## RoHS COMPLIANT

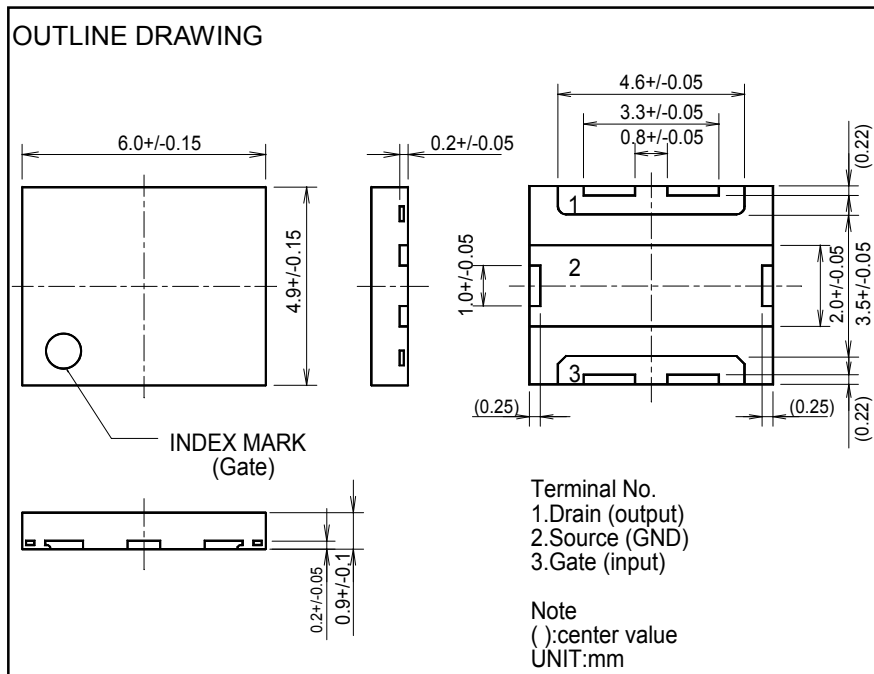
RD07MVS1B-101, T112 is a RoHS compliant product.

RoHS compliance is indicating by the letter "G" after the Lot Marking.

This product includes the lead in high melting temperature type solders.

However, it is applicable to the following exceptions of RoHS Directions.

1. Lead in high melting temperature type solders (i.e. tin-lead solder alloys containing more than 85% lead.)



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**ABSOLUTE MAXIMUM RATINGS**

(Tc=25°C UNLESS OTHERWISE NOTED)

| SYMBOL  | PARAMETER               | CONDITIONS       | RATINGS     | UNIT |
|---------|-------------------------|------------------|-------------|------|
| VDSS    | Drain to source voltage | Vgs=0V           | 30          | V    |
| VGSS    | Gate to source voltage  | Vds=0V           | +/- 20      | V    |
| Pch     | Channel dissipation     | Tc=25°C          | 50          | W    |
| Pin     | Input Power             | Zg=Zl=50Ω        | 1.5         | W    |
| ID      | Drain Current           | -                | 3           | A    |
| Tch     | Junction Temperature    | -                | 150         | °C   |
| Tstg    | Storage temperature     | -                | -40 to +125 | °C   |
| Rth j-c | Thermal resistance      | Junction to case | 2.5         | °C/W |

Note: Above parameters are guaranteed independently.

**ELECTRICAL CHARACTERISTICS** (Tc=25°C, UNLESS OTHERWISE NOTED)

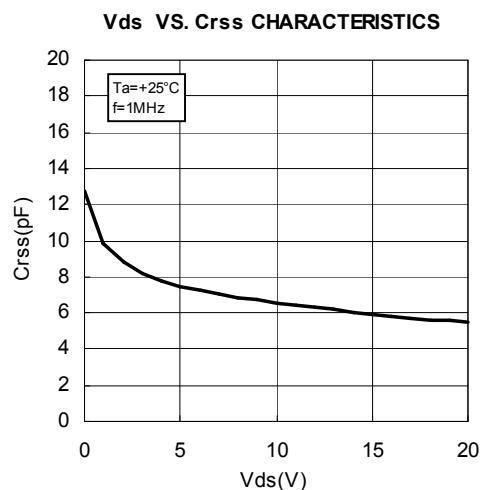
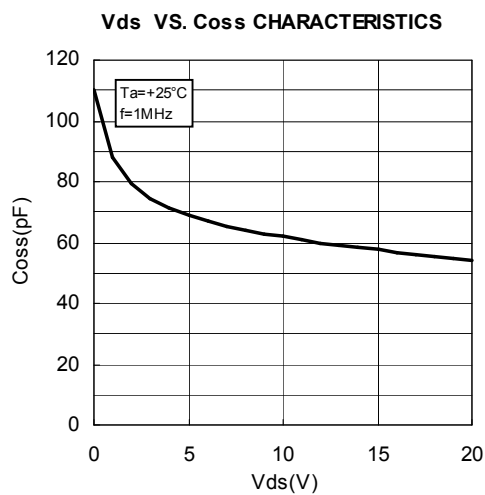
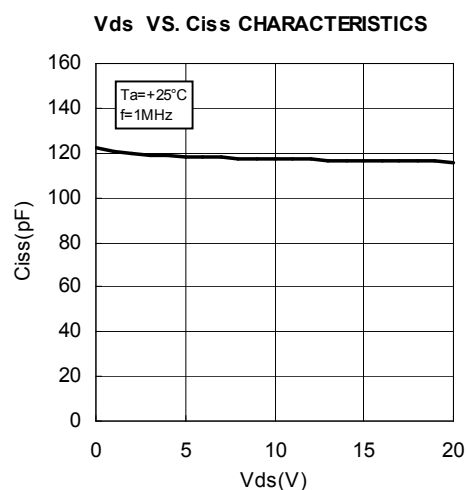
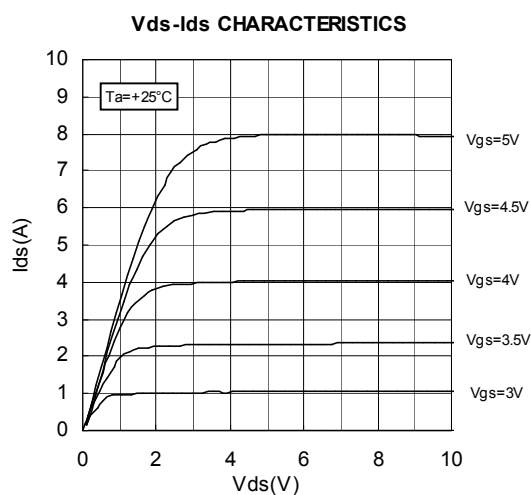
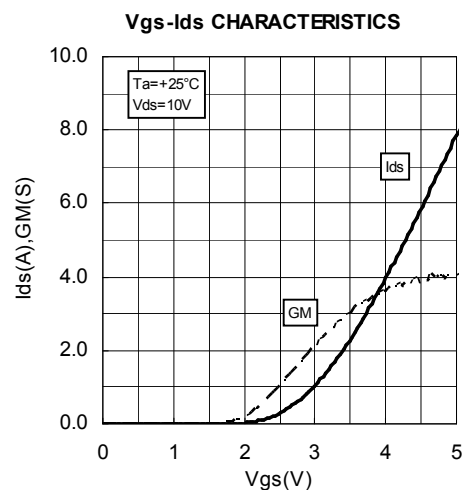
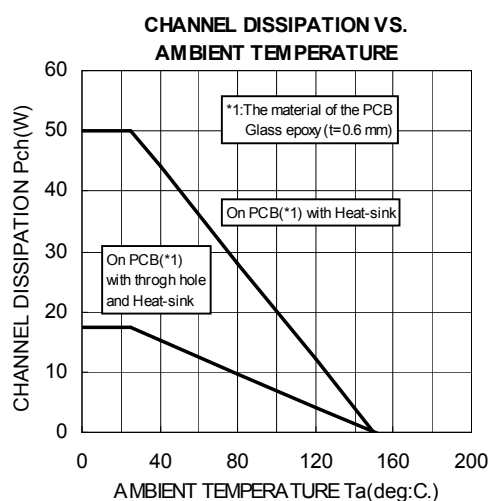
| SYMBOL | PARAMETER              | CONDITIONS                                                                               | LIMITS     |     |      | UNIT |
|--------|------------------------|------------------------------------------------------------------------------------------|------------|-----|------|------|
|        |                        |                                                                                          | MIN        | TYP | MAX. |      |
| IDSS   | Drain cutoff current   | VDS=17V, VGS=0V                                                                          | -          | -   | 200  | uA   |
| IGSS   | Gate cutoff current    | VGS=10V, VDS=0V                                                                          | -          | -   | 1    | uA   |
| VTH    | Gate threshold Voltage | VDS=12V, IDS=1mA                                                                         | 1.4        | 1.7 | 2.4  | V    |
| Pout1  | Output power           | f=175MHz, VDD=7.2V                                                                       | 7          | 8   | -    | W    |
| ηD1    | Drain efficiency       | Pin=0.3W, Idq=700mA                                                                      | 55         | 60  | -    | %    |
| Pout2  | Output power           | f=520MHz, VDD=7.2V                                                                       | 7          | 8   | -    | W    |
| ηD2    | Drain efficiency       | Pin=0.7W, Idq=750mA                                                                      | 50         | 55  | -    | %    |
|        | Load VSWR tolerance    | VDD=9.2V, Po=7W(Pin Control)<br>f=175MHz, Idq=700mA, Zg=50Ω<br>Load VSWR=20:1(All Phase) | No destroy |     |      | -    |
|        | Load VSWR tolerance    | VDD=9.2V, Po=7W(Pin Control)<br>f=520MHz, Idq=750mA, Zg=50Ω<br>Load VSWR=20:1(All Phase) | No destroy |     |      | -    |

Note: Above parameters, ratings, limits and conditions are subject to change.

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## TYPICAL CHARACTERISTICS

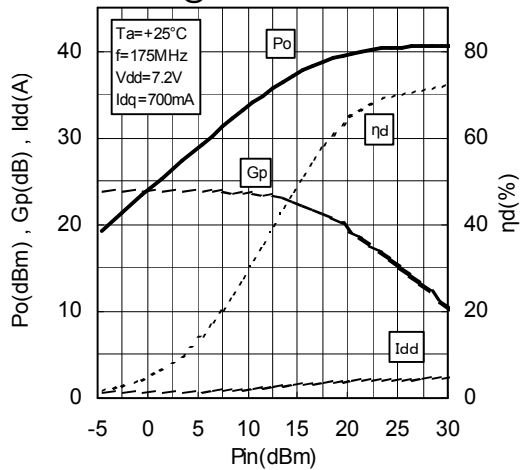


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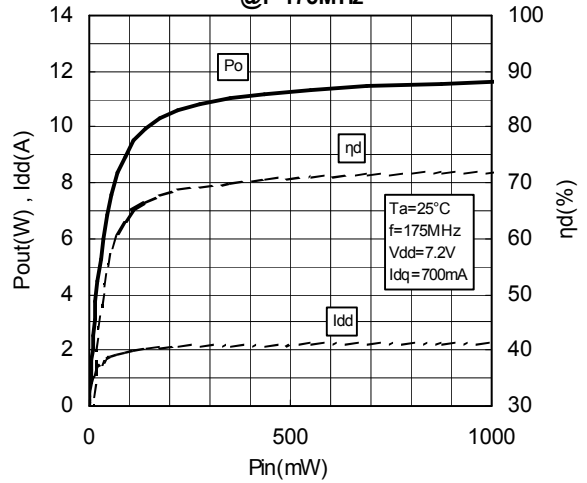
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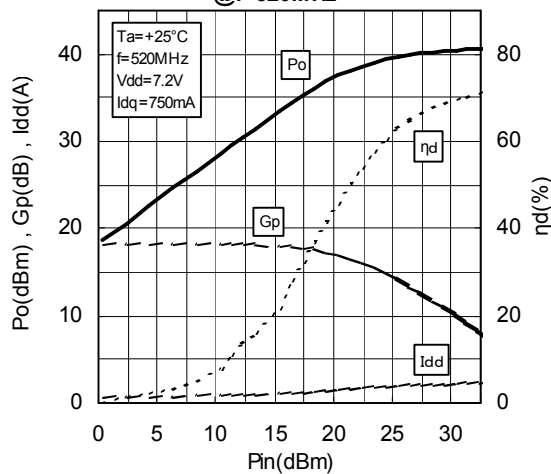
Pin-Po CHARACTERISTICS  
@f=175MHz



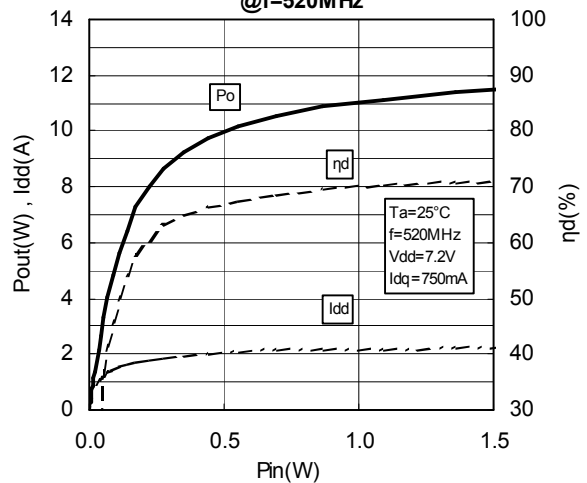
Pin-Po CHARACTERISTICS  
@f=175MHz



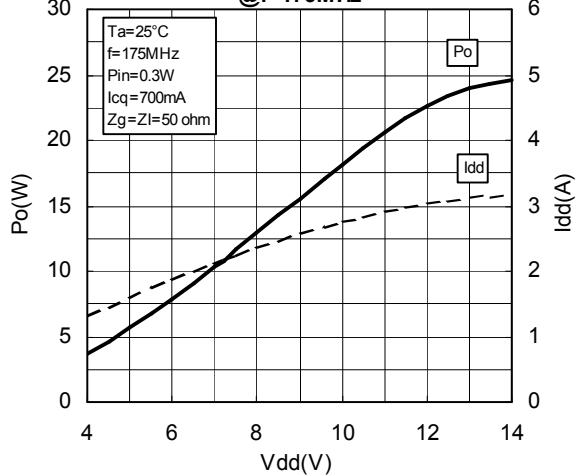
Pin-Po CHARACTERISTICS  
@f=520MHz



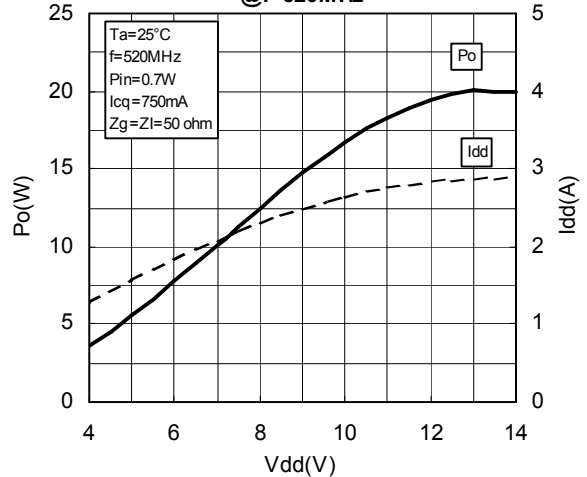
Pin-Po CHARACTERISTICS  
@f=520MHz



Vdd-Po CHARACTERISTICS  
@f=175MHz



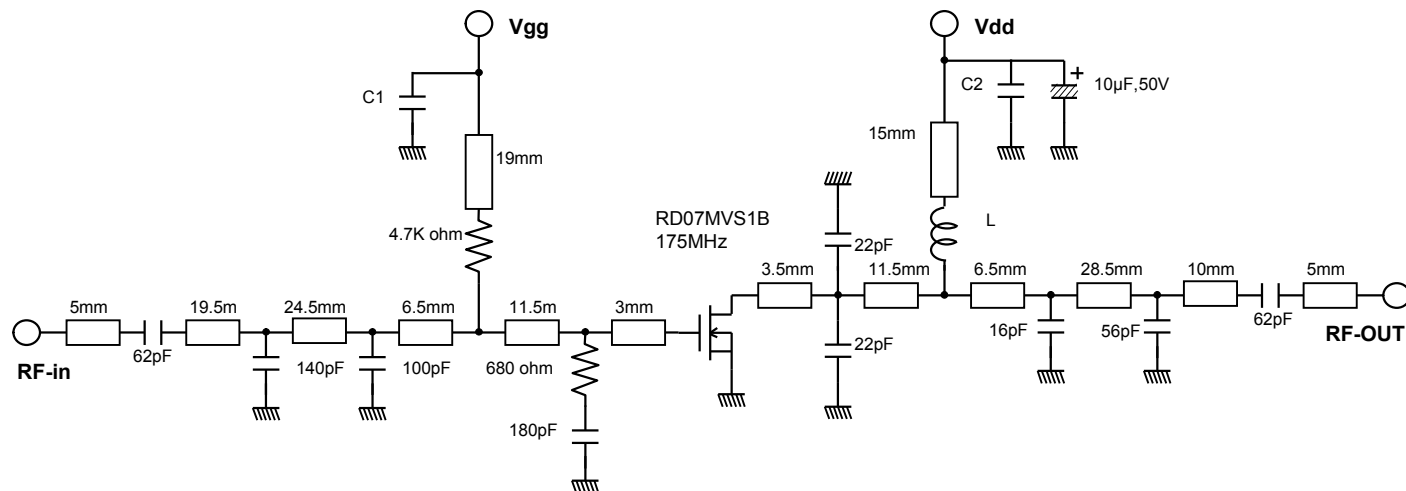
Vdd-Po CHARACTERISTICS  
@f=520MHz



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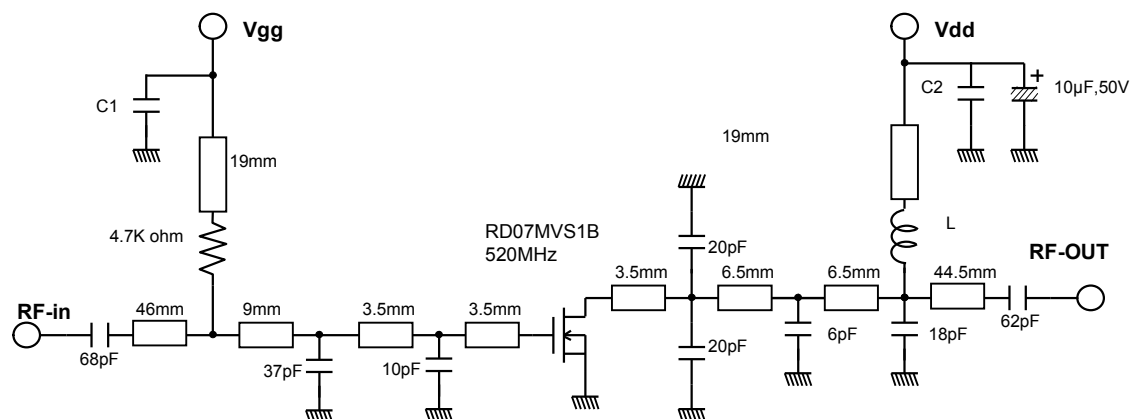
## TEST CIRCUIT(f=175MHz)



L: Enameled wire 7 Turns, D: 0.43mm, 2.46mm O.D  
C1, C2: 1000pF, 0.0022µF in parallel

Note: Board material PTFE substrate  
Micro strip line width=2.2mm/50 ohm, er: 2.7, t=0.8mm  
W: line width=1.0mm

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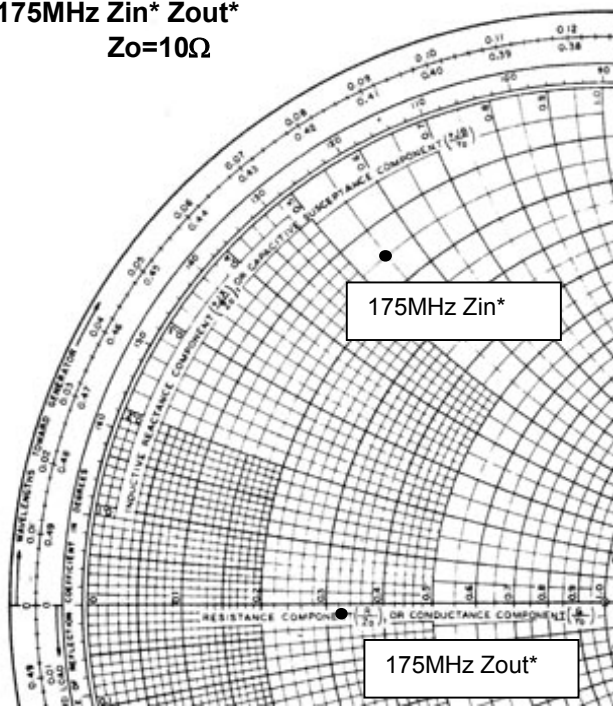
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## INPUT/OUTPUT IMPEDANCE VS. FREQUENCY CHARACTERISTICS

175MHz  $Z_{in}^*$   $Z_{out}^*$   
 $Z_o=10\Omega$

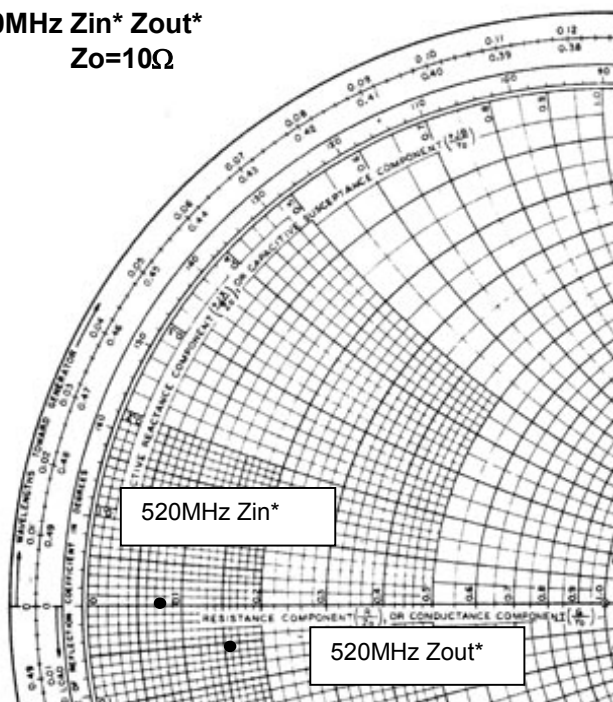


$V_{dd}=7.2V$ ,  $I_{dq}=700mA$ ( $V_{gg}$  adj.),  $P_{in}=0.28W$

$Z_{in}^*=1.55+j5.53$   
 $Z_{out}^*=3.24-j0.26$

$Z_{in}^*$ : Complex conjugate of input impedance  
 $Z_{out}^*$ : Complex conjugate of output impedance

520MHz  $Z_{in}^*$   $Z_{out}^*$   
 $Z_o=10\Omega$



$V_{dd}=7.2V$ ,  $I_{dq}=750mA$ ( $V_{gg}$  adj.),  $P_{in}=0.7W$

$Z_{in}^*=0.76+j0.06$   
 $Z_{out}^*=1.61-j0.52$

$Z_{in}^*$ : Complex conjugate of input impedance  
 $Z_{out}^*$ : Complex conjugate of input impedance

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**RD07MVS1B S-PARAMETER DATA (@V<sub>dd</sub>=7.2V, I<sub>d</sub>=750mA)**

| Freq.<br>[MHz] | S11   |        | S21   |       | S12   |       | S22   |        |
|----------------|-------|--------|-------|-------|-------|-------|-------|--------|
|                | (mag) | (ang)  | (mag) | (ang) | (mag) | (ang) | (mag) | (ang)  |
| 100            | 0.881 | -174.0 | 6.055 | 75.9  | 0.018 | -14.2 | 0.767 | -170.7 |
| 135            | 0.885 | -175.5 | 4.358 | 68.8  | 0.017 | -20.6 | 0.773 | -172.2 |
| 150            | 0.888 | -176.0 | 3.844 | 66.2  | 0.017 | -23.4 | 0.774 | -172.4 |
| 175            | 0.891 | -176.6 | 3.207 | 62.8  | 0.016 | -26.8 | 0.788 | -172.4 |
| 200            | 0.896 | -177.1 | 2.749 | 59.3  | 0.016 | -29.8 | 0.810 | -172.4 |
| 250            | 0.904 | -178.0 | 2.069 | 51.8  | 0.015 | -36.7 | 0.829 | -173.0 |
| 300            | 0.914 | -178.8 | 1.602 | 46.2  | 0.013 | -42.2 | 0.842 | -173.6 |
| 350            | 0.922 | -179.7 | 1.288 | 40.5  | 0.012 | -47.7 | 0.871 | -174.6 |
| 400            | 0.929 | 179.6  | 1.043 | 35.7  | 0.011 | -52.2 | 0.878 | -175.3 |
| 450            | 0.934 | 178.8  | 0.864 | 31.8  | 0.009 | -55.2 | 0.895 | -176.3 |
| 500            | 0.939 | 178.0  | 0.724 | 27.7  | 0.008 | -57.6 | 0.907 | -177.1 |
| 520            | 0.941 | 177.8  | 0.678 | 26.4  | 0.008 | -57.8 | 0.907 | -177.4 |
| 527            | 0.941 | 177.7  | 0.660 | 26.0  | 0.007 | -59.8 | 0.908 | -177.4 |
| 550            | 0.944 | 177.4  | 0.616 | 24.7  | 0.007 | -61.0 | 0.910 | -177.8 |
| 600            | 0.947 | 176.7  | 0.529 | 21.7  | 0.006 | -62.4 | 0.925 | -178.8 |
| 650            | 0.950 | 176.1  | 0.458 | 19.1  | 0.005 | -63.3 | 0.925 | -179.3 |
| 700            | 0.953 | 175.5  | 0.401 | 16.8  | 0.005 | -63.4 | 0.933 | 180.0  |
| 750            | 0.953 | 174.9  | 0.351 | 14.4  | 0.004 | -63.4 | 0.939 | 179.4  |
| 800            | 0.956 | 174.5  | 0.314 | 12.6  | 0.003 | -61.4 | 0.940 | 179.1  |
| 850            | 0.955 | 174.1  | 0.279 | 10.9  | 0.003 | -59.7 | 0.944 | 178.3  |
| 900            | 0.958 | 173.6  | 0.250 | 9.1   | 0.002 | -59.3 | 0.948 | 178.3  |
| 950            | 0.959 | 173.4  | 0.225 | 8.1   | 0.002 | -54.8 | 0.947 | 177.7  |
| 1000           | 0.959 | 172.9  | 0.204 | 6.3   | 0.001 | -47.5 | 0.952 | 177.2  |
| 1050           | 0.959 | 172.7  | 0.186 | 5.3   | 0.001 | -34.8 | 0.951 | 177.2  |
| 1100           | 0.959 | 172.5  | 0.170 | 3.9   | 0.001 | -14.2 | 0.952 | 176.5  |

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## ATTENTION:

1. High Temperature ; This product might have a heat generation while operation. Please take notice that there is a possibility to receive a burn to touch the operating product directly or touch the product until cold after switch off. At the near the product, do not place the combustible material that has possibilities to arise the fire.
2. Generation of High Frequency Power ; This product generates a high frequency power. Please take notice that do not leakage the unnecessary electric wave and use this product without cause damage for human and property per normal operation.
3. Before use; Before use the product, please design the equipment in consideration of the risk for human and electric wave obstacle for equipment.

## PRECAUTIONS FOR THE USE OF MITSUBISHI SILICON RF POWER DEVICES:

1. The specifications of mention are not guarantee values in this data sheet. Please confirm additional details regarding operation of these products from the formal specification sheet. For copies of the formal specification sheets, please contact one of our sales offices.
2. RA series products (RF power amplifier modules) and RD series products (RF power transistors) are designed for consumer mobile communication terminals and were not specifically designed for use in other applications. In particular, while these products are highly reliable for their designed purpose, they are not manufactured under a quality assurance testing protocol that is sufficient to guarantee the level of reliability typically deemed necessary for critical communications elements and In the application, which is base station applications and fixed station applications that operate with long term continuous transmission and a higher on-off frequency during transmitting, please consider the derating, the redundancy system, appropriate setting of the maintain period and others as needed. For the reliability report which is described about predicted operating life time of Mitsubishi Silicon RF Products, please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor.
3. RD series products use MOSFET semiconductor technology. They are sensitive to ESD voltage therefore appropriate ESD precautions are required.
4. In the case of use in below than recommended frequency, there is possibility to occur that the device is deteriorated or destroyed due to the RF-swing exceed the breakdown voltage.
5. In order to maximize reliability of the equipment, it is better to keep the devices temperature low. It is recommended to utilize a sufficient sized heat-sink in conjunction with other cooling methods as needed (fan, etc.) to keep the channel temperature for RD series products lower than 120deg/C (in case of  $T_{chmax}=150deg/C$ ), 140deg/C (in case of  $T_{chmax}=175deg/C$ ) under standard conditions.
6. Do not use the device at the exceeded the maximum rating condition. In case of plastic molded devices, the exceeded maximum rating condition may cause blowout, smoldering or catch fire of the molding resin due to extreme short current flow between the drain and the source of the device. These results causes in fire or injury.
7. For specific precautions regarding assembly of these products into the equipment, please refer to the supplementary items in the specification sheet.
8. Warranty for the product is void if the products protective cap (lid) is removed or if the product is modified in any way from its original form.
9. For additional "Safety first" in your circuit design and notes regarding the materials, please refer the last page of this data sheet.
10. Please refer to the additional precautions in the formal specification sheet.

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Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

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